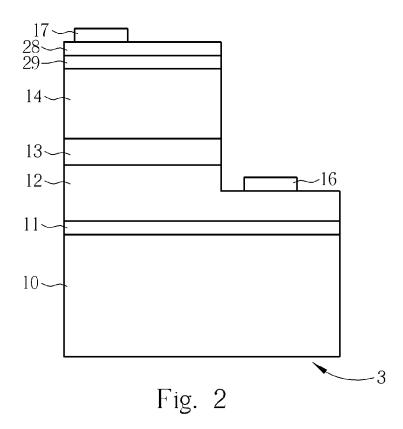


Page	1	6	οf	30	
ı ayc	•	U	O1	50	



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ı agc	•	J	O1	50	

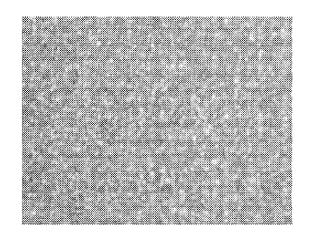


Fig. 3

Page	20	٥f	30	
raye	20	UI	<b>J</b> U	

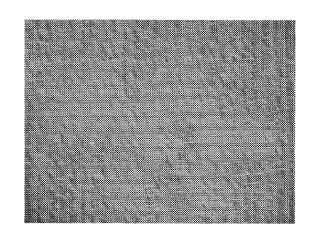


Fig. 4

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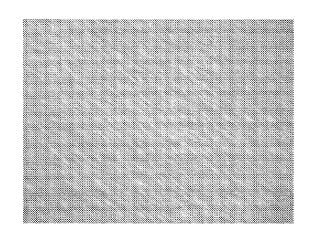


Fig. 5

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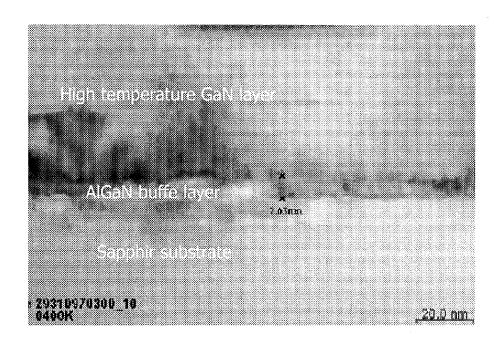


Fig. 6

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1 aye	20	O1	50	

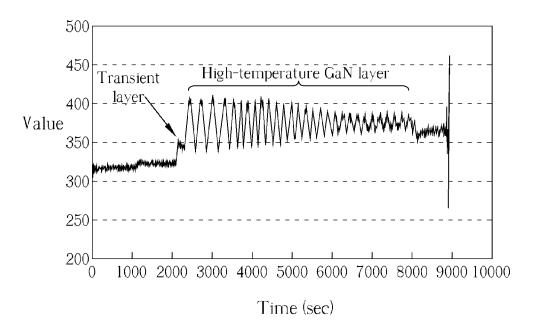


Fig. 7

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1 aye	20	Oi	50	

	Brightness at 20mA (mcd)	Forward bias at 20mA (V)	Leakage current at -5V (μA)	Reverse voltage at -10V (V)
Buffer provided by two-step growth method	37~40	3.14~3.25	0.00~0.01	24~32
Ternary nitride-based buffer layer provided by the present invention	38~42	3.17~3.24	0.00~0.01	20~33

Fig. 8

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